Small Signal MOSFET

25 V, 0.75 A, Single, N−Channel, ESD Protection, SC−70/SOT−323

LNTS4409NWT1G
S-LNTS4409NWT1G

SC-70

Features

- Advance Planar Technology for Fast Switching, Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- This is a Pb−Free Device
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

Applications

- Boost and Buck Converter
- Load Switch
- Battery Protection

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
25 V	249 mΩ @ 4.5 V	0.75 A
	299 mΩ @ 2.7 V	

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	25	V
Gate−to−Source Voltage			V_{GS}	±8.0	V
Drain Current	t < 5 s	T_A = 25°C	I_D	0.75	A
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	0.7	A
		T_A = 75°C		0.6	
Power Dissipation (Note 1)	Steady State		P_D	0.28	W
Power Dissipation (Note 1)	t ≤ 5 s		P_D	0.33	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	3.0	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to +150	°C
Source Current (Body Diode) (Note 1)			I_S	0.3	A
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C
ESD Rating − Machine Model				250	V

THERMAL RESISTANCE RATINGS

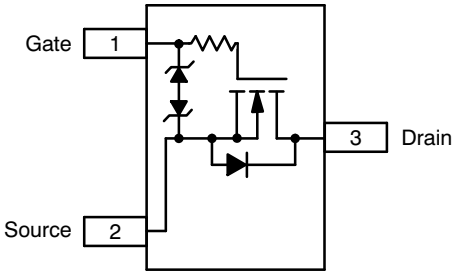
Rating	Symbol	Max	Unit
Junction−to−Ambient – Steady State (Note 1)	$R_{\theta JA}$	450	°C/W
Junction−to−Ambient − t ≤ 5 s (Note 1)	$R_{\theta JA}$	375	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

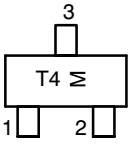
PIN CONNECTIONS

SC−70 (3−Leads)



(Top View)

MARKING DIAGRAM



T4 = Specific Device Code
M = Month Code

Device	Package	Shipping
LNTS4409NWT1G S-LNTS4409NWT1G	SC−70 (Pb−Free)	3000/Tape & Reel

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		25			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				30		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 20 V	T_J = 25°C			0.5	μA
			T_J = 70°C			2.0	
			T_J = 125°C			5.0	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 8.0 V				3	uA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		0.5		1.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				−2.0		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 0.6 A			249	350	mΩ
		V_{GS} = 2.7 V, I_D = 0.2 A			299	400	
		V_{GS} = 4.5 V, I_D = 1.2 A			260		
Forward Transconductance	g_{FS}	V_{DS} = 5.0 V, I_D = 0.5 A			0.5		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 10 V			49	60	pF
Output Capacitance	C_{OSS}				22.4	30	
Reverse Transfer Capacitance	C_{RSS}				8.0	12	
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 0.8 A			1.2	1.5	nC
Threshold Gate Charge	$Q_{G(TH)}$				0.2		
Gate−to−Source Charge	Q_{GS}				0.28	0.50	
Gate−to−Drain Charge	Q_{GD}				0.3	0.40	
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 0.7 A, R_G = 51 Ω			5.0	12	ns
Rise Time	t_r				8.2	8.0	
Turn−Off Delay Time	$t_{d(OFF)}$				23	35	
Fall Time	t_f				41	60	
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 0.6 A	T_J = 25°C		0.82	1.20	V

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

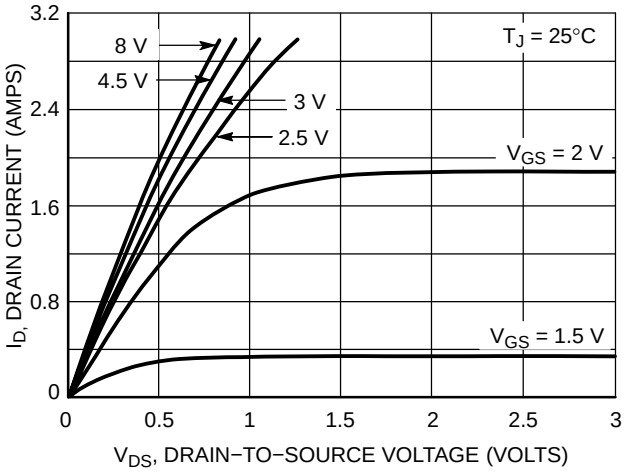

Figure 1. On−Region Characteristics

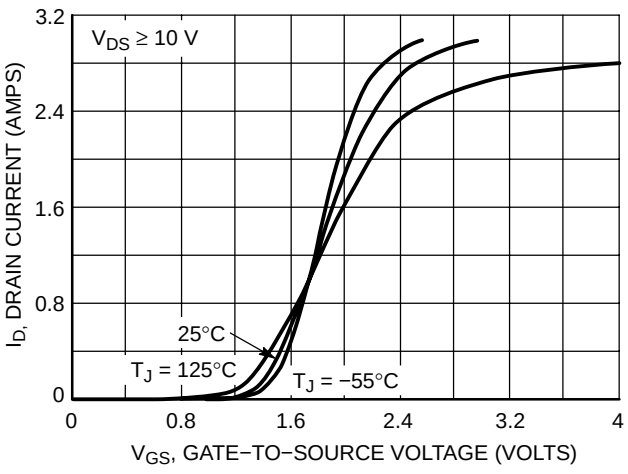

Figure 2. Transfer Characteristics

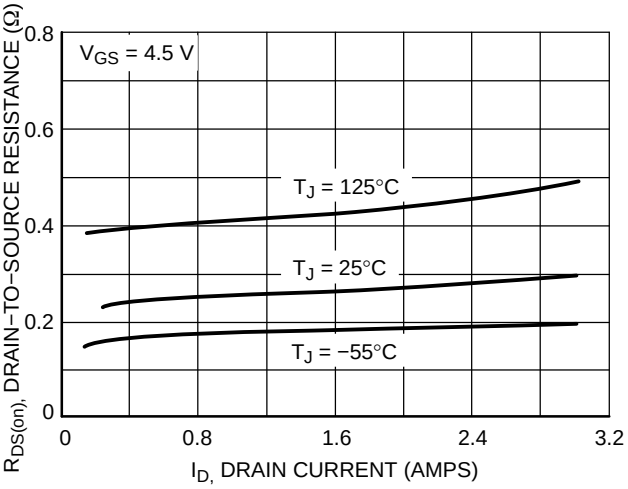

Figure 3. On−Resistance vs. Drain Current and Temperature

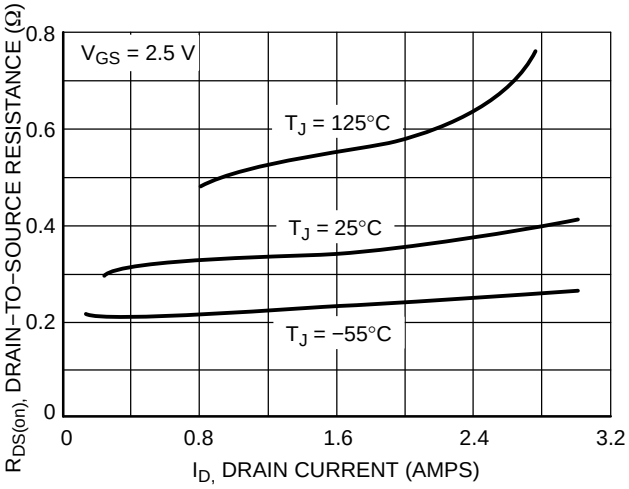

Figure 4. On−Resistance vs. Drain Current and Gate Voltage

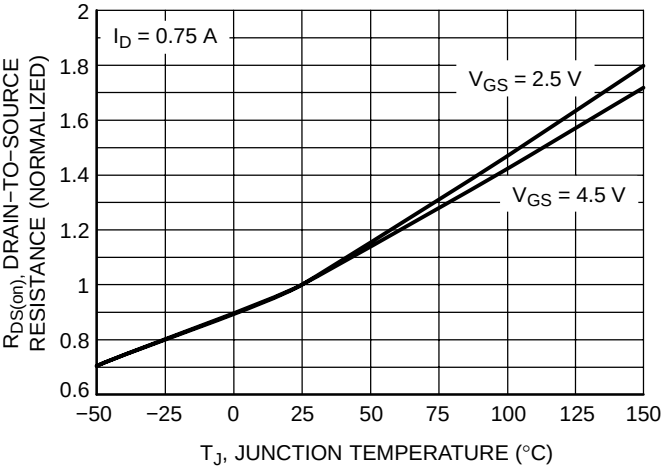

Figure 5. On−Resistance Variation with Temperature

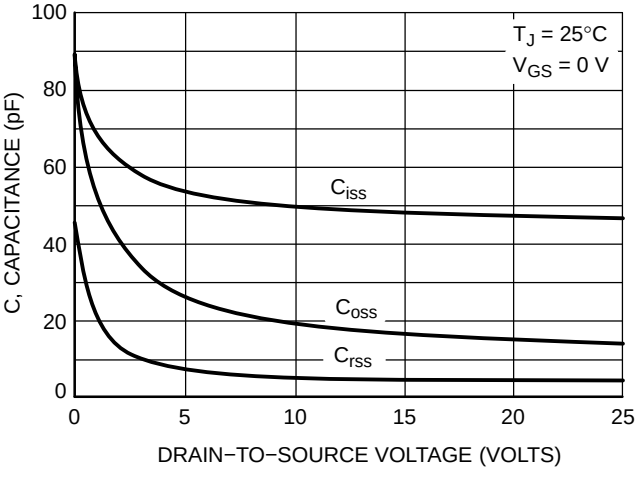

Figure 6. Capacitance Variation

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

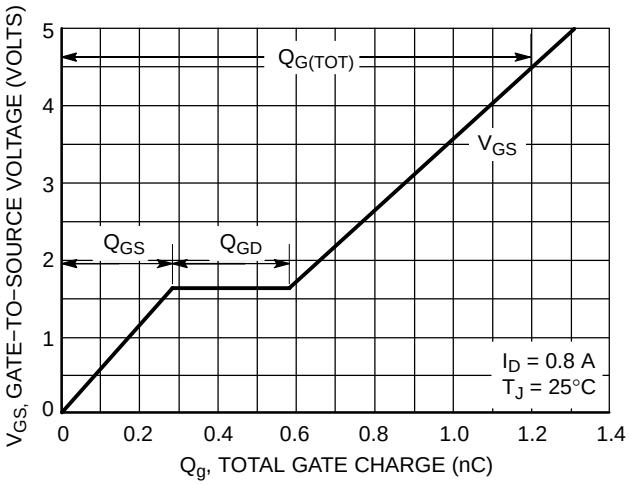

Figure 7. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

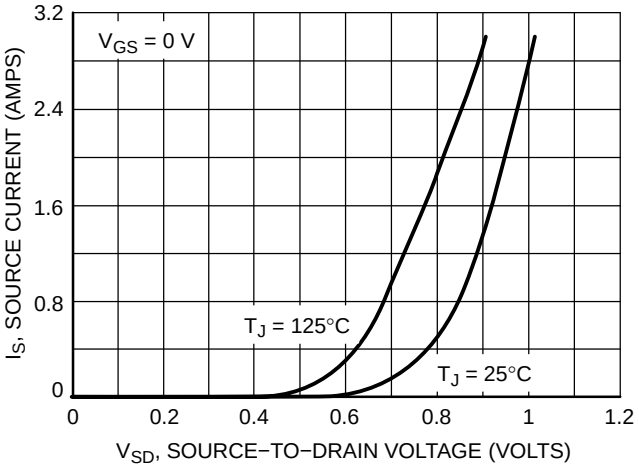

Figure 8. Diode Forward Voltage vs. Current

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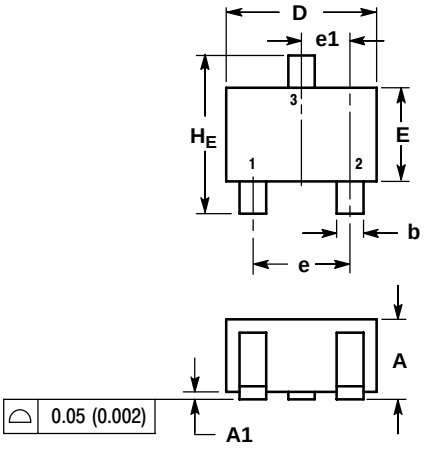
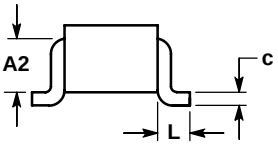
PACKAGE DIMENSIONS

SC−70 (SOT−323)





NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.7 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	
L		0.425 REF			0.017 REF	
H_E	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*